

# Real Design Challenges of Low Power Physical Design Implementation



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Senior Design Engineer  
Munich 15th May 2007

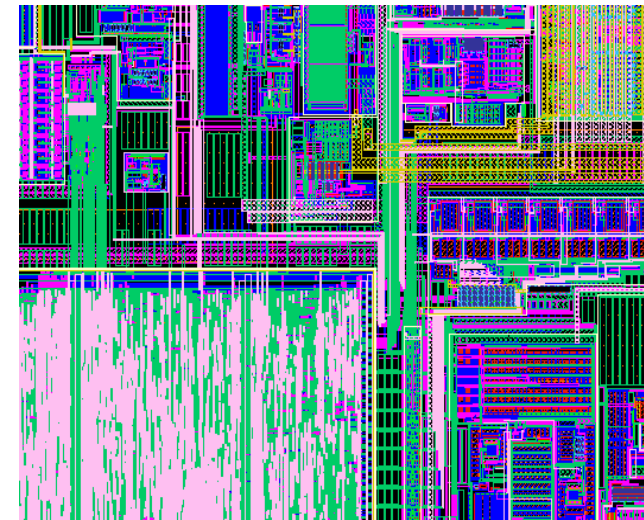


- **Stefano Piccioni, Senior Design Engineer at S3 (Silicon & Software Systems)**
- **Worked in Accent (Milan) since 2000 before joining S3 (Dublin) in 2005**
- **8 years experience in RTL to gds2 ASIC flow**
- **Bachelor Degree in Physics from "Universita' degli Studi di Bologna", Italy**
- **Master Degree in 'Microelectronics and Systems' from "Universita' degli Studi di Catania", Italy**

- **The Connected Consumer Technology Company**
  - Enabling the delivery of next generation products and services to the consumer, at home and on the move
- **Founded in 1986**
  - 4 Design Centres (Ireland x 2, Czech Republic, Poland)
  - 300 Employees
  - Sales offices and representatives globally
- **Trusted by the world's leading technology companies**
  - Deliver cutting-edge design solutions on time



- **Global Leader in 90 and 65nm IC Design**
  - More than 30 Designs in 90nm
  - Mixed Analog / Digital SoC Focus
  - “First Production 65nm tapeout” - EETimes
  - On schedule, right-first-time silicon
- **Serving Top Tier Clients**
  - Including NXP, Texas Instruments
  - 4 of Top 5 IDMs and 3 of Top 5 Fabless
- **Teaming with Leading Technology Partners**
  - Including TSMC, IBM, Cadence, ARM, UMC



# Presentation Overview



- **Low power techniques**
- **Testcase Introduction**
- **Design Challenges**
- **Conclusions**

# Low Power Techniques - Overview

- With new mobile devices power consumption has become an hot topic
- New handsets are very complex devices and need high performance together with low power consumption
- Battery life represents an important feature in choosing a product in the market but has not been improved as expected by modern technologies
- That's the reason why is important to minimize device power consumption using new design techniques



- Different **low power techniques** can be **applied throughout the design cycle**, from architectural level down to physical implementation
- EDA vendors together with silicon vendors offer a wide range of design solutions and libraries targeted to low power
- Power consumption concurrently optimized together with Area and Timing
- **Principal Low Power Techniques** are
  - Clock Gating and Operand Isolation
  - Leakage Optimization and use of Multi VT Libraries
  - MSMV with automatic insertion of level shifters

# Low Power Techniques – Power Consumption

- **Power consumption is a sum of Dynamic + Static contributors**

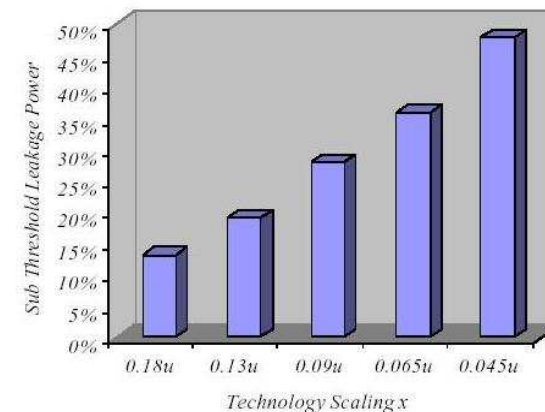
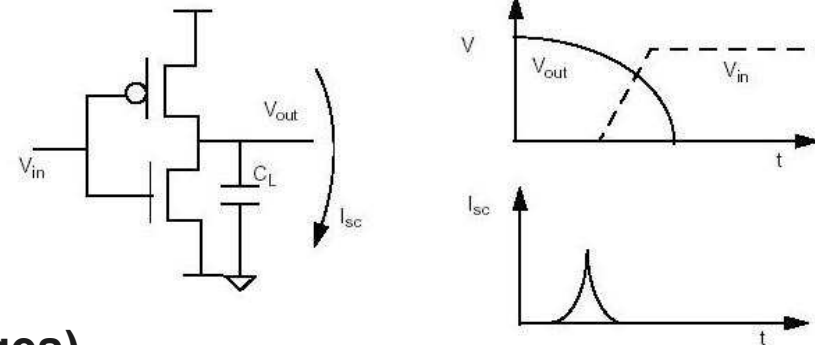
- **Dynamic power consumption**  
(power consumed during state changes)

- **Internal power** dissipation, which includes switching of the transistors inside the cell and the power dissipated when charging or discharging internal net capacitances

- **Net power** includes switching power consumed by charging and discharging the chip wires capacitance

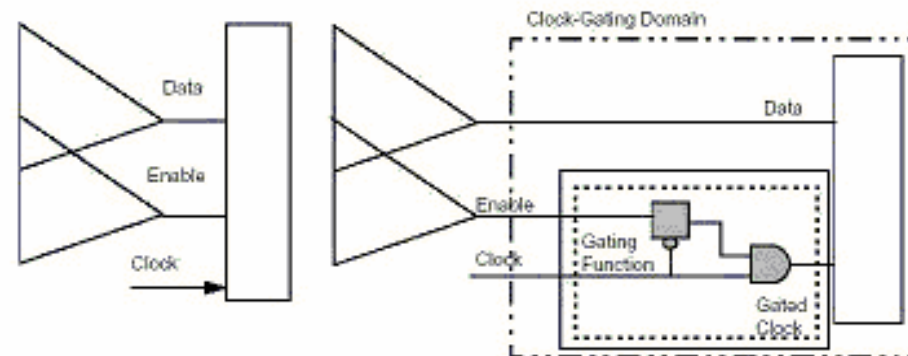
- **Static power consumption**  
(power statically dissipated)

- **Leakage power** dissipation of the cell, With today's technology shrinking down to 90 nm and below, the leakage power becomes more and more dominant.



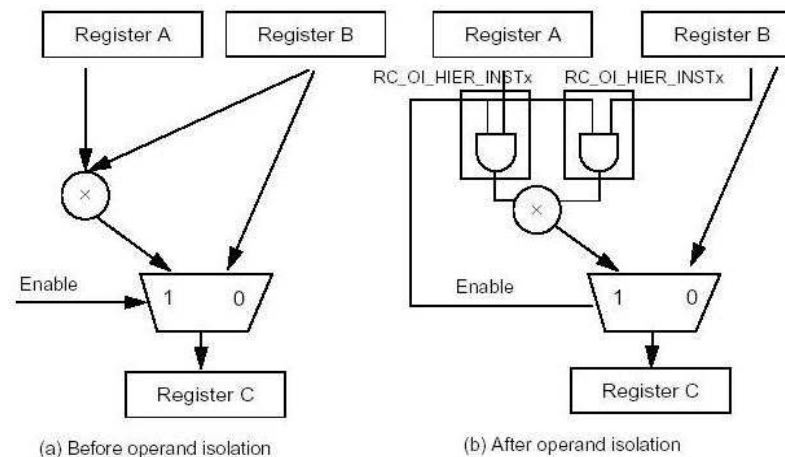
## Low Power Techniques – Clock Gating

- Even if data is loaded into registers very infrequently in most designs, **the clock signal continues to toggle at every clock cycle**
- Gating a group of flip-flops that are enabled by the same control signal **reduces unnecessary clock toggles**
- In the idle period **power is saved in the gated-clock circuitry** (typically portion of clock tree and registers)



## Low Power Techniques – Operand Isolation

- **Operand Isolation** is a **dynamic power optimization** technique that can reduce power dissipation in **datapath blocks** controlled by an enable signal.
- Its main purpose is to **shutdown (isolate) the function unit (operand)** when its results are not used



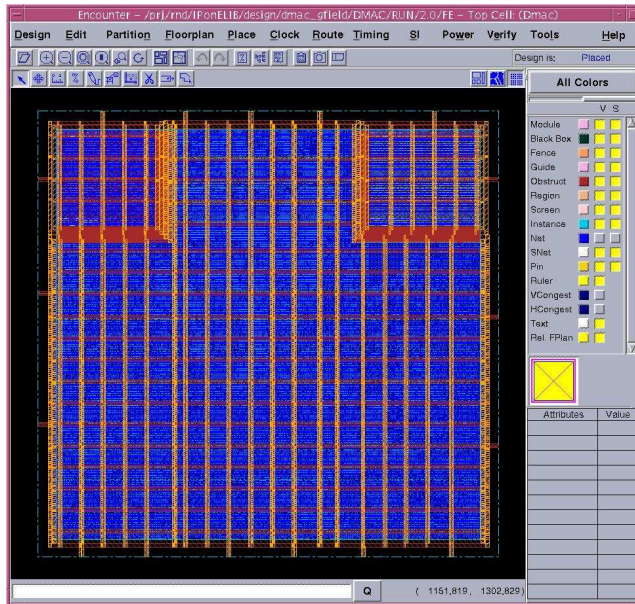
• *Example:* When the Enable is off, register C only uses the result of register B, but the multiplier continues its computations. Because the multiplier dissipates the most power, the total amount of power wasted is quite significant.

- Consist mainly in **using different libraries** with different voltage thresholds (typically LowVT and HighVT) in order to reduce leakage power consumption:
  - *LVT cells are **faster** but **dissipate more** leakage power*
  - *HVT cells are **slower** but **dissipate less** leakage power*
- Different **synthesis** approaches can be used
- **Physical implementation** is performed mostly **using HVT**, **limiting LVT cells** only where it is not possible to close timing
- After final routing, an usual IPO consists in **replacing LVT cells with HVT cells with same footprint**, so no re-routing is required

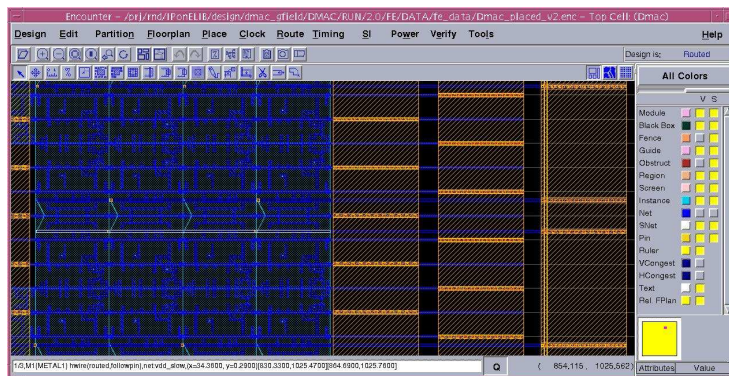
- It is possible to use in the same design **different voltage islands** that can be **switched on/off individually** or **supplied with different voltages**
- **Dynamically switching off entire modules** when not used has a bigger impact on power savings because **all leakage power consumption completely disappears**
- The need to accommodate multiple power domains and multiple voltage levels makes **low-power chip design much more complex**
- **MSMV capable tools are needed** to assist the designer at every step of the flow

- **A typical MSMV flow involves:**
  - Floorplanning and power domains definitions
  - Insertion of level shifters (and isolation cells) at RTL or netlist level
  - Placement of level shifters (and isolation cells) in correct power domain and additional followpin connections
  - MSMV and power aware optimization
  - Clock tree insertion that takes into account different domains and low power techniques
  - Power analysis and Irdrop run on different grids
  - DRC / LVS check and formal verification considering different voltage supplies

# Low Power Techniques – MSMV Examples

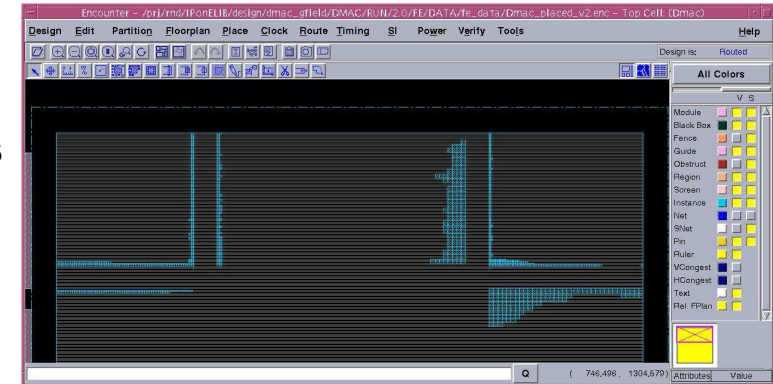


**Floor-planning and  
Power Domains creation**

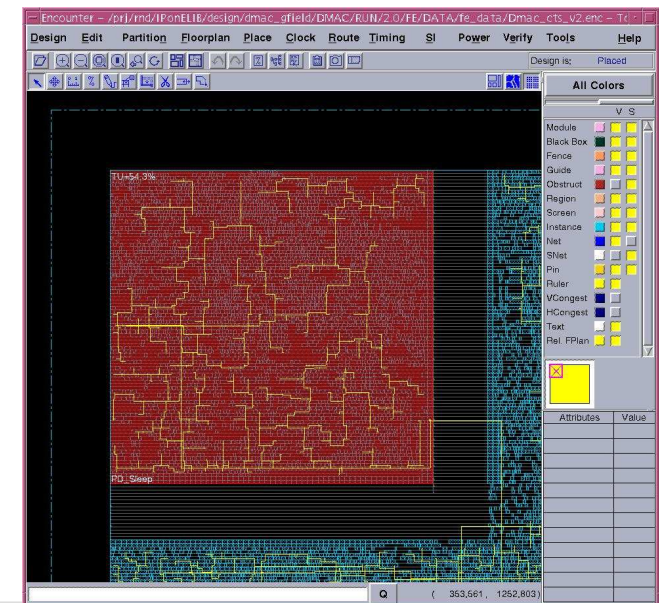


**Level Shifters additional  
power pin connection**

**Level Shifters  
placement**



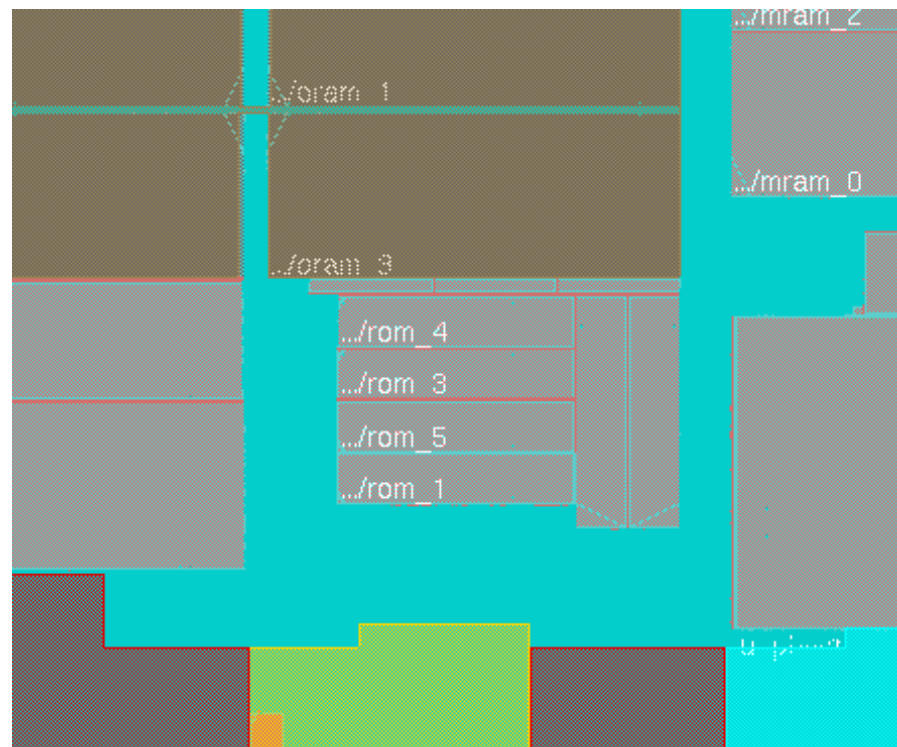
**Clock Tree  
insertion with  
MSMV**



- **Overview**
- **Design Tasks**
- **Power Domains**
- **Isolation Cell Handling**
- **Power Switch Handling**
- **Power Grid Design**
- **Power Estimation and Analysis**
- **Physical Verification**

# Test Case Overview

- **Technology:**
  - 90nm
  - 6 metal layers
- **Target Die Area:**
  - 21sq.mm
  - ~1Mgates
- **Power Domains:**
  - Several gated PD
  - 1 always on
- **Target IR drop:**
  - 10% (5%vdd+5%vss)
- **Priority:**
  - Area
  - Power
  - Performance



- **Synthesis (RC)**
  - High-Vt library only
- **Floorplanning (SoCE)**
  - IO planning
  - Power domains grid planning
- **P&R (SoCE)**
  - Isolation cell placement
  - Power domain aware CTS/opt.
  - Power domain crossing checks (S3 script)
  - Power domain aware filler insertion (H/L Leakage decap)
  - Allow standard-Vt library for manual fixes (not in AO PD)
- **STA/SI (F&I/PT-SI/CeltIC)**
- **PV/FV (Calibre/Conformal)**
- **Power/IRDrop Analysis (Powermeter/Vstorm)**

- Power management domain is ‘always on’ and is defined as default power domain
- Multiple independently power switchable domains
- High connectivity between ‘always on’ and other domains created high placement density near domains boundaries
- Choosing the domain shapes that minimize congestion took a considerable amount of time and resulted in very irregular shapes



- Isolation cells have been inserted on all nets crossing gated power domains to the 'always-on' domain (>1000)

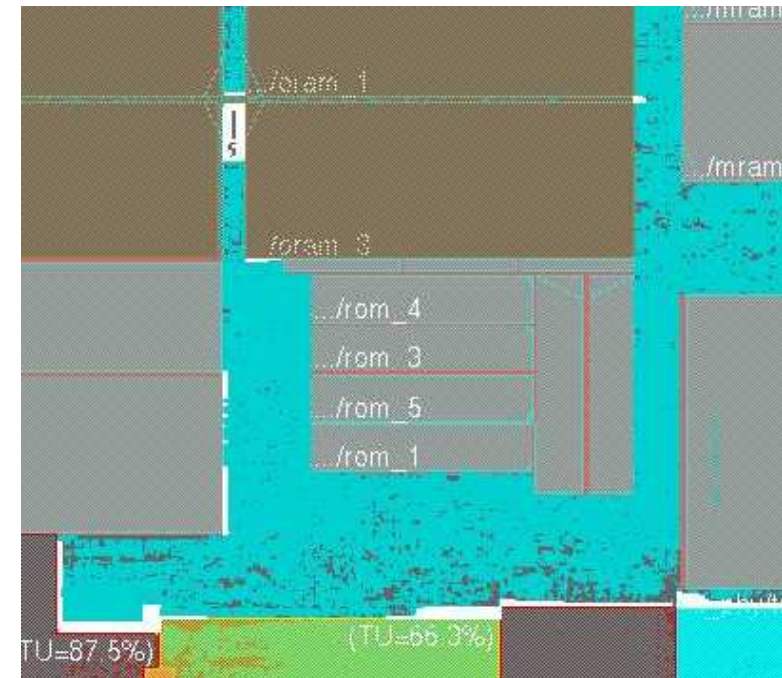
```
#####  
# Specify Isolation Cells #  
#####  
specifyIsolationCell -cell {ISO_OR2_8}  
specifyIsolationCell -cell {ISO_NR2B_8}  
specifyIsolationCell -cell {ISO_AN2_8}
```

- It has been checked that iso cells have been correctly recognized using:

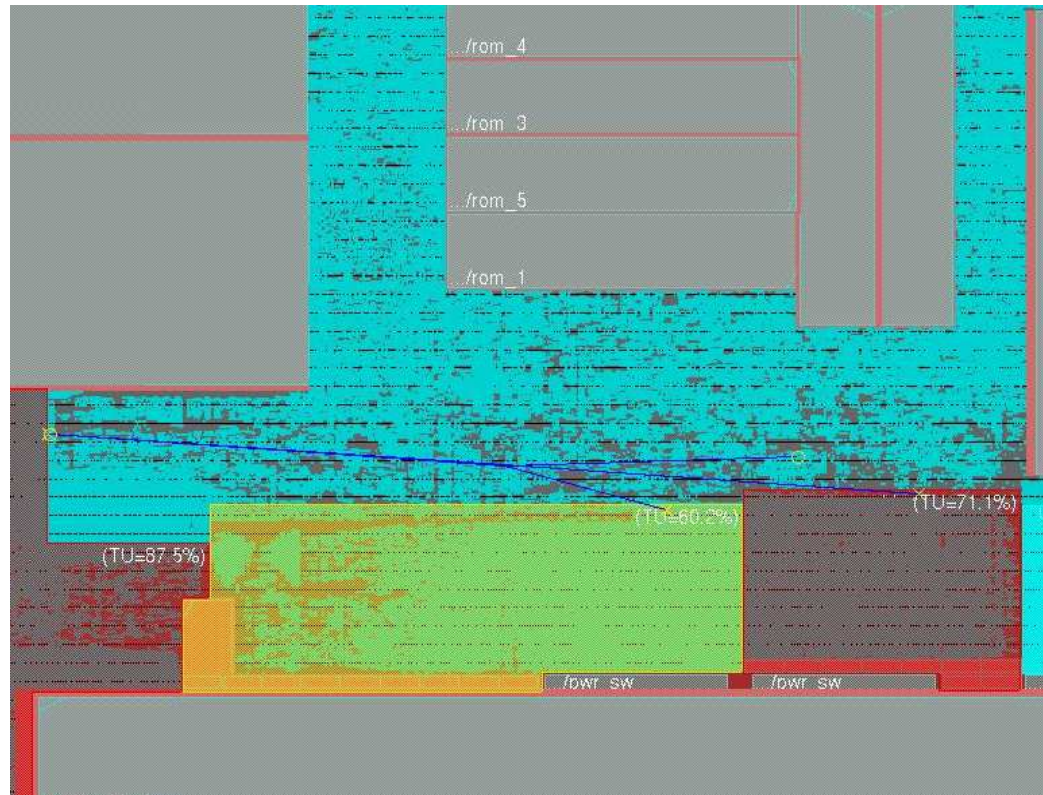
```
reportIsolation -outfile isolationcells.rpt
```

- Then we placed them together with all the logic and then highlight them with:

```
reportIsolation -highlight
```

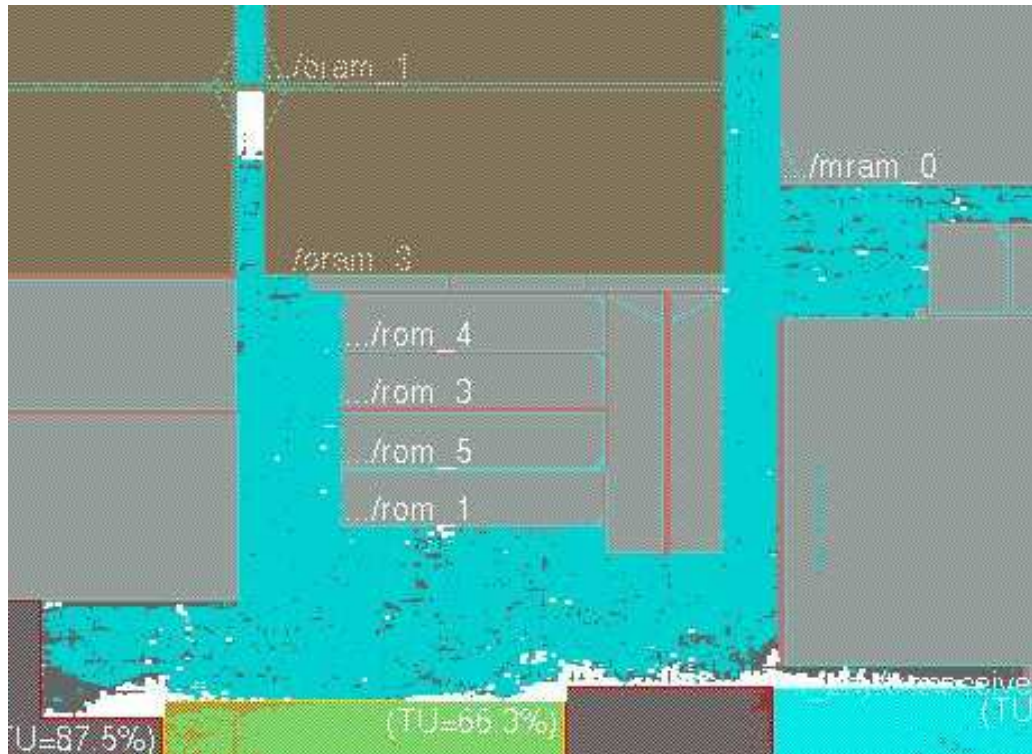


# Testcase - Isolation Cells Placement



- Not really a good job!
- Encounter (5.2USR1) seems to place iso cells putting more effort in spreading them near the PD boundary rather than placing them based on connectivity
- Isolation cells are placed one near each near to the PD border but It happens that some of them are placed far away from the driver
- This could creates drv violations and bad timing

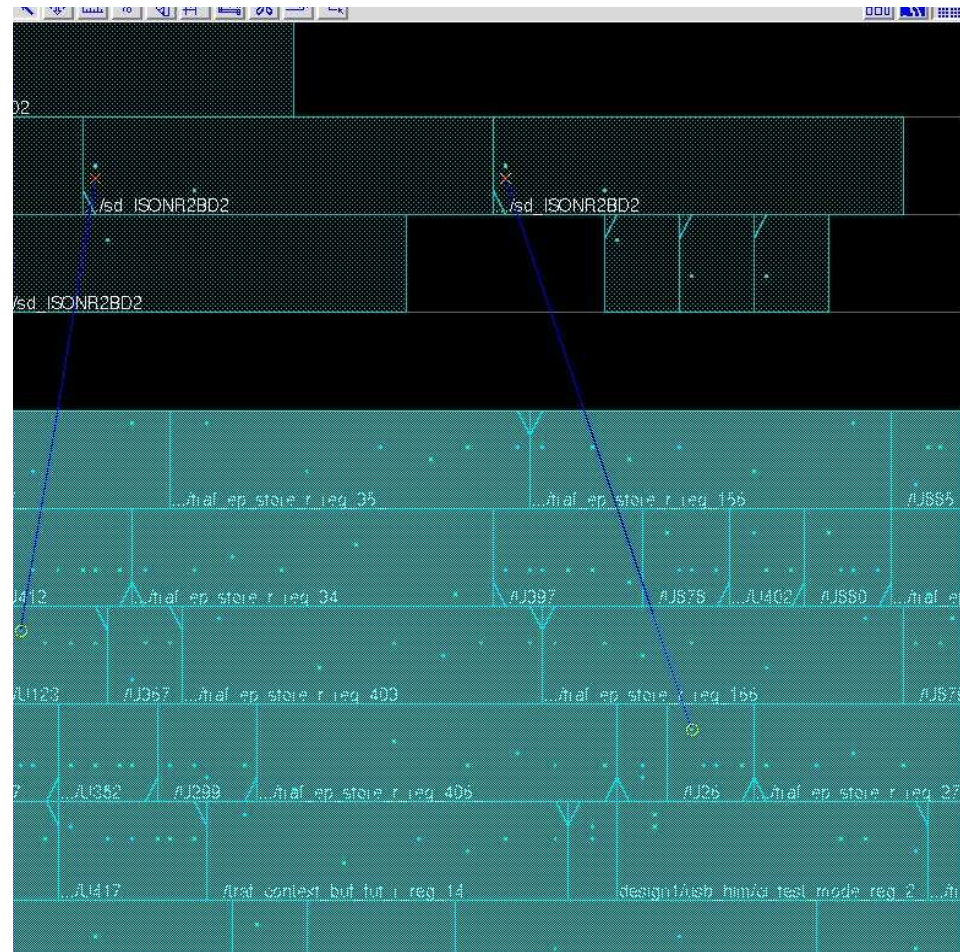
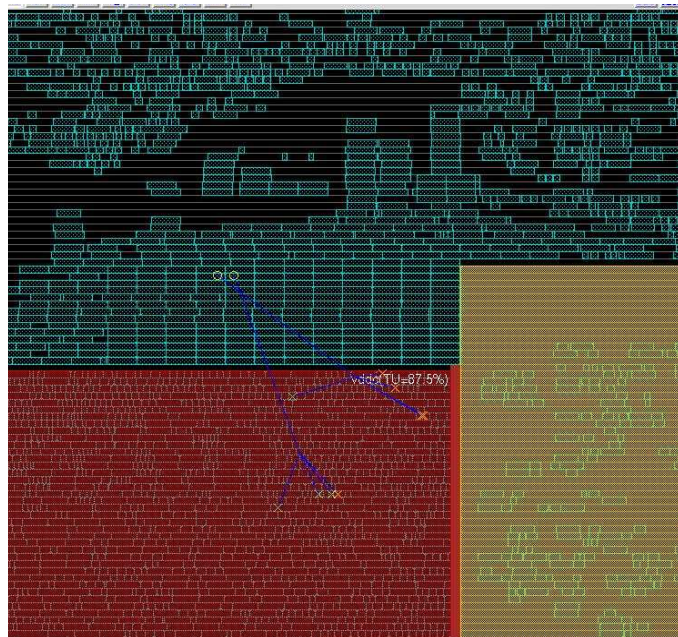
## Testcase - Isolation Cells Placement



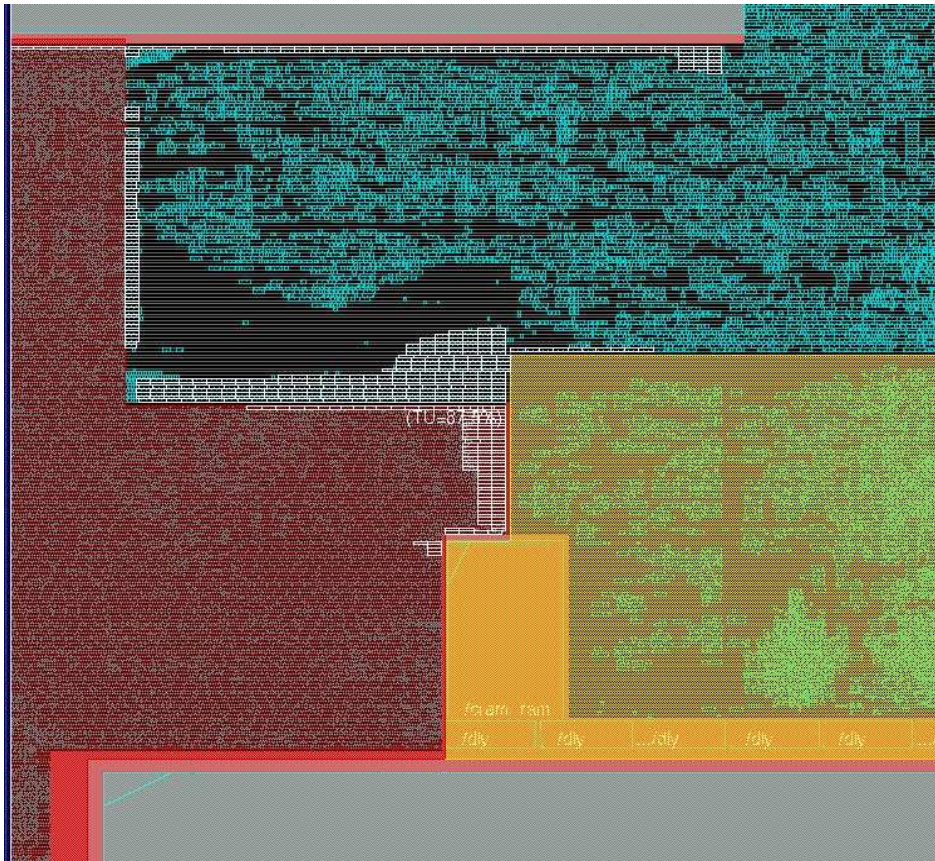
- Cadence was contacted to solve this issue and with SoCE version 5.2USR2 isolation cell placement has been improved
- In the meanwhile we used another approach as a workaround
- Names of all nets crossing power domains were identified and given a weight (max value 512) before placement
- A *set\_dont\_touch* assertion was also added to prevent buffer insertion on those nets

# Testcase - Isolation Cells Placement

- As a result isolation cells placement was more 'connection' driven
- Now length of all nets is minimized through placement of isolation cells as close as possible to the logic they talk to

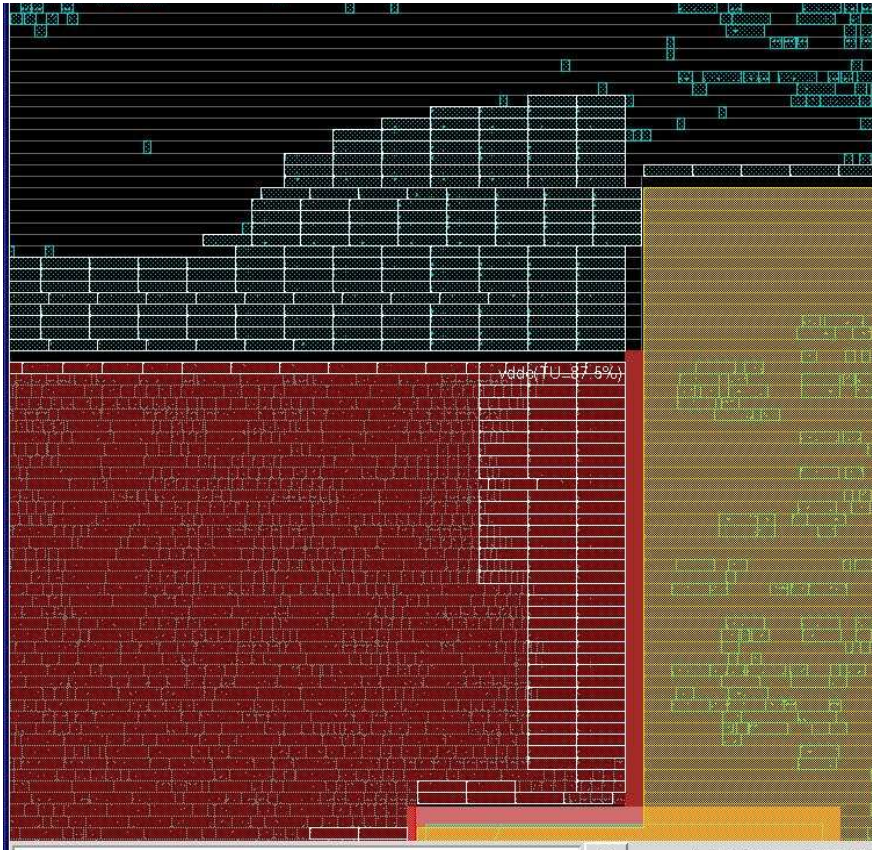


# Testcase - Isolation Cells Placement



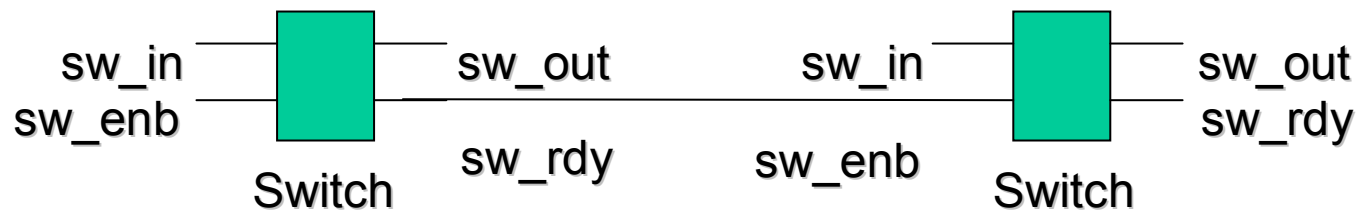
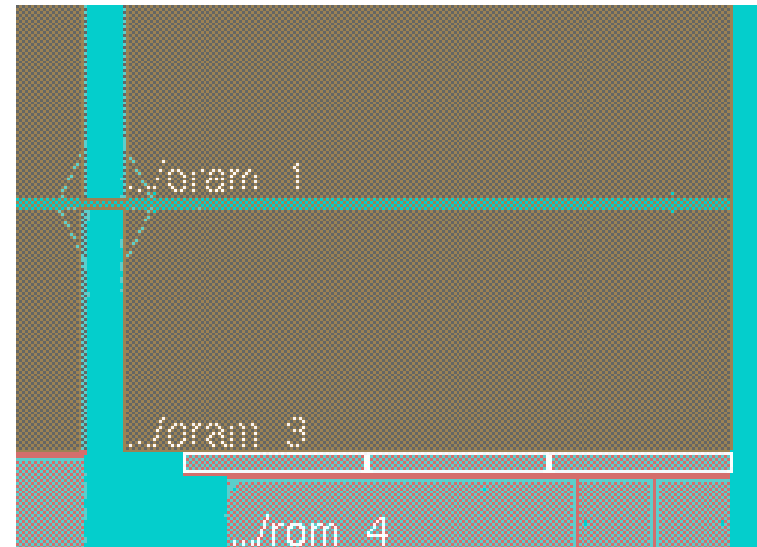
- A bug was discovered during post placement optimization with SoCE version 5.2USR1
- During optimization isolation cells were moved without any reason and new placement often was not 'legal' because was inside one of the switchable power domains
- Only way to avoid this behaviour was to fix the placement before running optimization
- This was not the ideal solution because encounter was no longer free to move cells as needed in order to close timing

## Testcase - Isolation Cells Placement



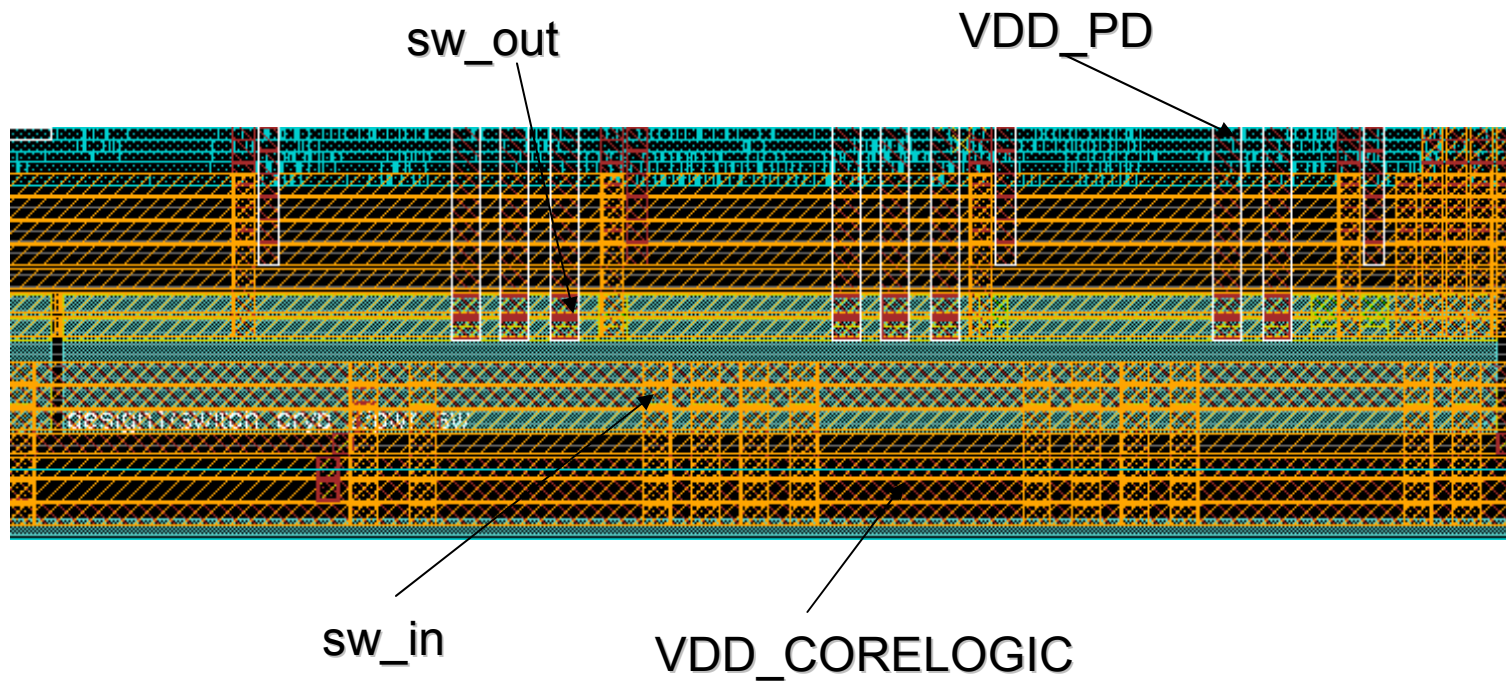
- Cadence was contacted in order to fix this bug and they discovered a problem with '*refinePlacement*' (placement legalization) during optimization and fixed it
- Cadence sent us a pre-release version of Encounter that solved the issue and let us tape out in time
- Also this problem was definitely solved with SoCE version 5.2USR2

- **On-chip voltage regulator**
- **Power switches (nr)**
  - 2ohm resistance (rs)
  - Max 5% IR drop (p)
  - $nr \geq (k * ng * c * f * rs) / p$
- **Cascaded switching**
  - switch\_ready asserted 2us after switch enable to slowly turn on power switches minimizing voltage drop

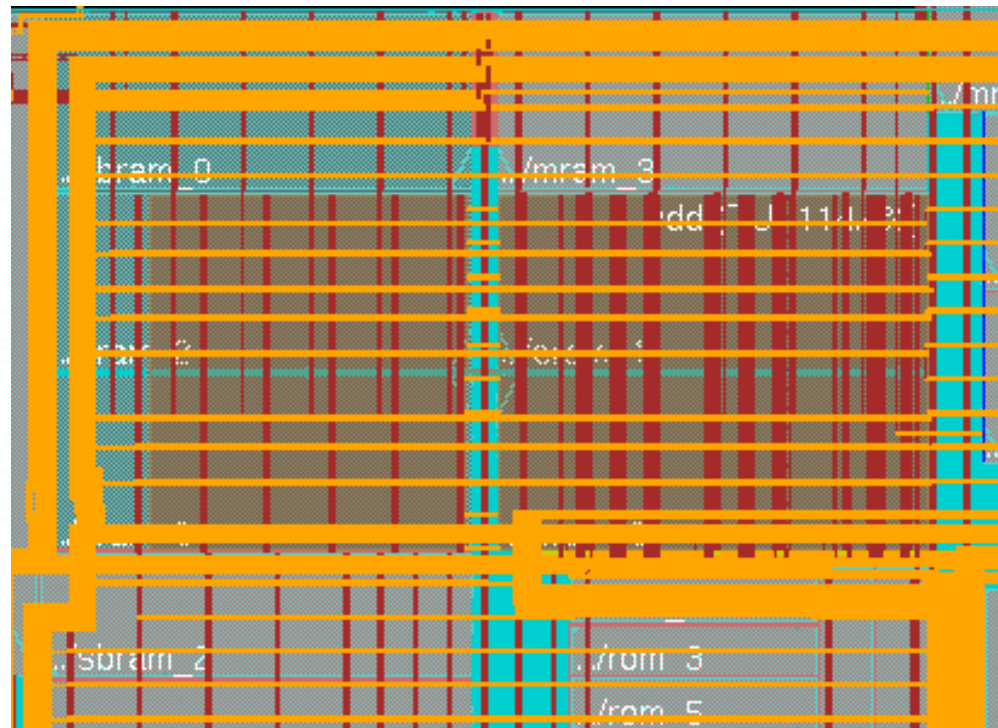


- **Power switches layout guidelines**

- Max 30mA output requirement
- Use of M3-M6 metal layers

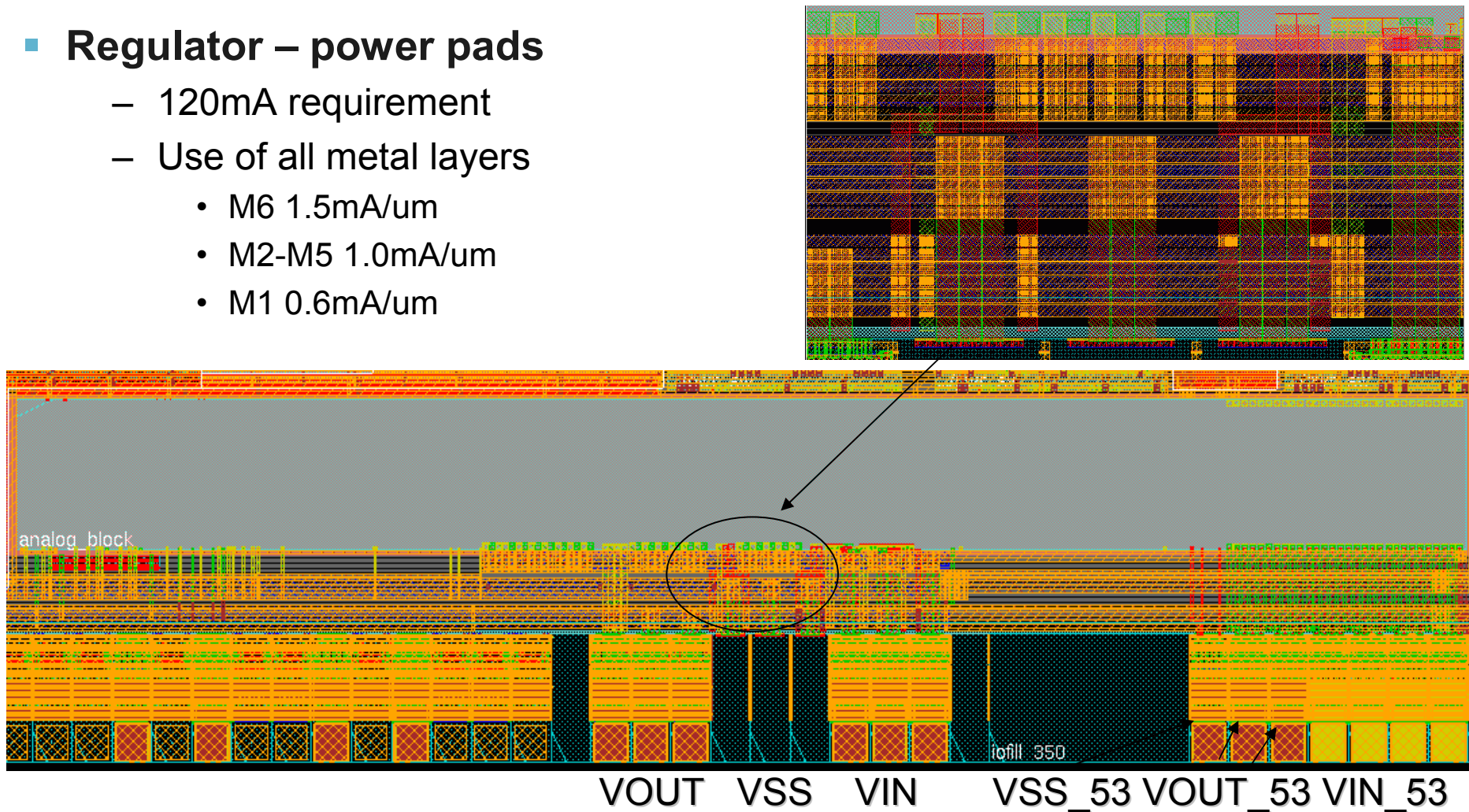


- Power island grids
- Regulator – pads grid
- Power switches connection
- Core grid
  - Incl. always-on island
- IO ring
- RAMs grids / rings
- Analog macro hook-up

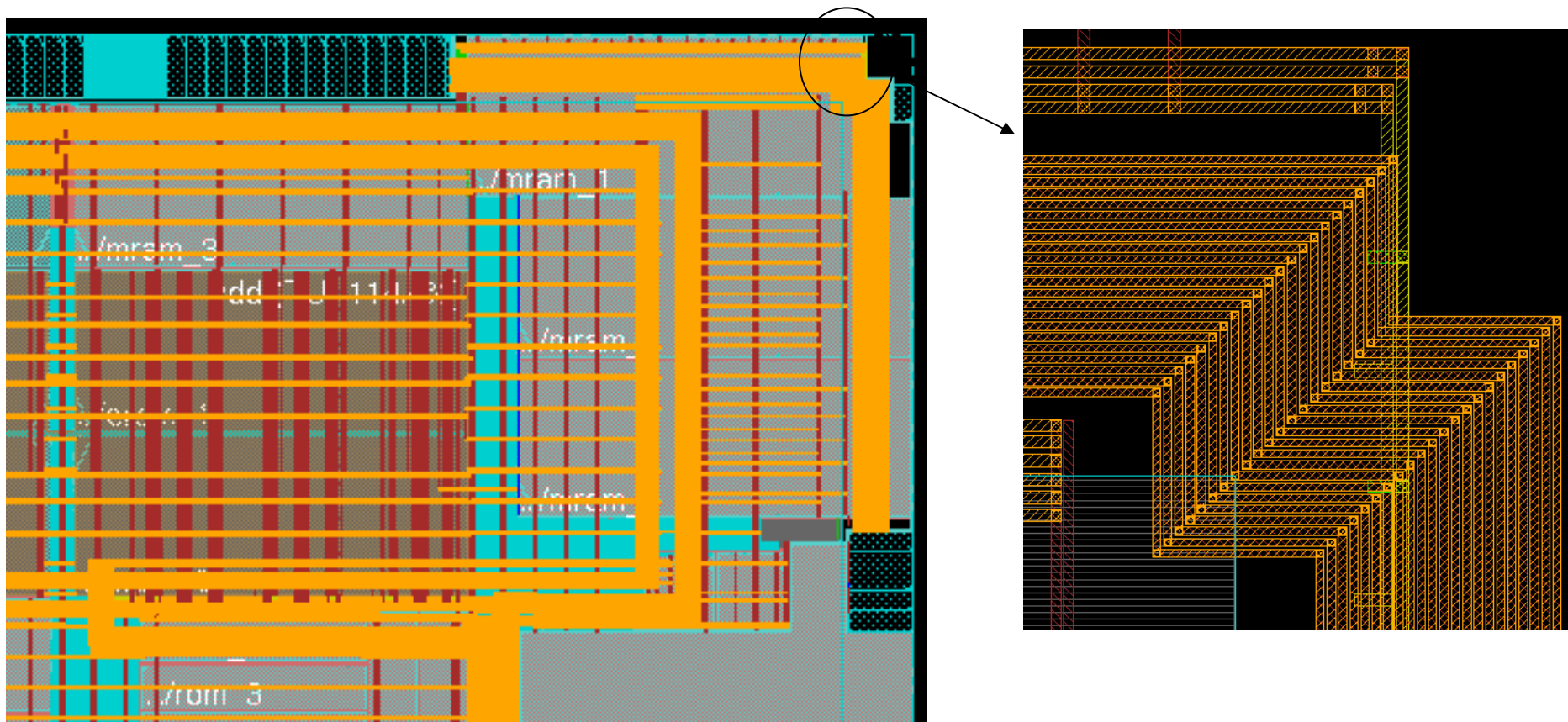


- **Regulator – power pads**

- 120mA requirement
- Use of all metal layers
  - M6 1.5mA/um
  - M2-M5 1.0mA/um
  - M1 0.6mA/um



- IO, Rams and core grids



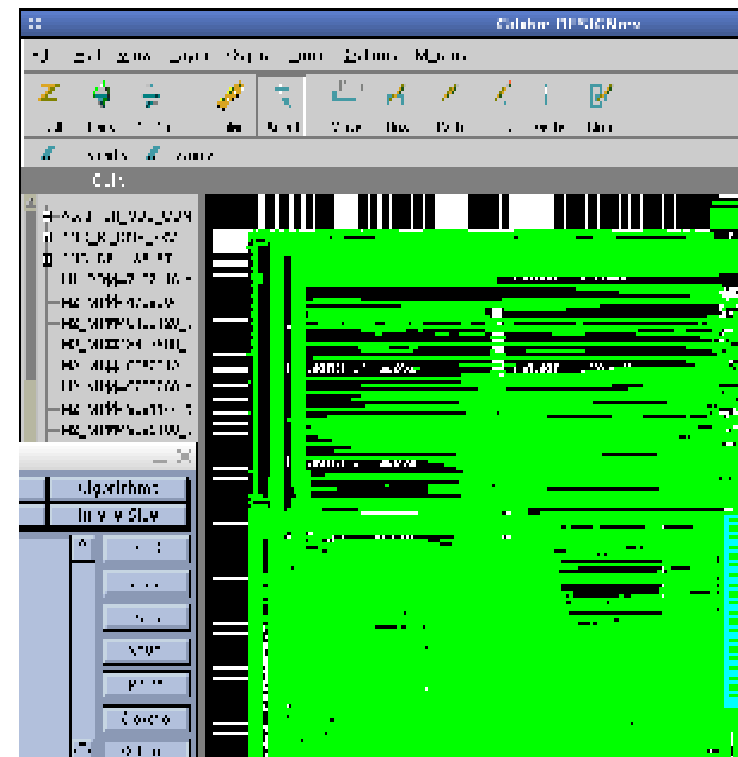
# Power Measurement and Analysis

- **Power measurement**
  - Powermeter upgraded to cadence\_anls 6.1
  - Now fully power aware
  - ~200mW consumption
- **Power analysis**
  - Vstorm updated to cadence\_anls 6.1
  - Supports analysis through power switches
  - Multiple power-gate dependent runs
  - IR drop requirements met after iterations



- **LVS**

- Text points for power domains



- **Low power techniques permeate every step in implementation flow**
- **MSMV involves a more complex flow with additional resources required and possible impact on schedule**
- **‘Young’ features, designer need to work closer to EDA vendor**
- **Routing congestion could get worse due to power islands**
- **Timing closure more difficult with level shifters**
- **New type of possible errors, new type of checks**
- **Better equipped for low power implementation**

# Thank you!

- QUESTION?

